

isc N-Channel MOSFET Transistor

2SK844

DESCRIPTION

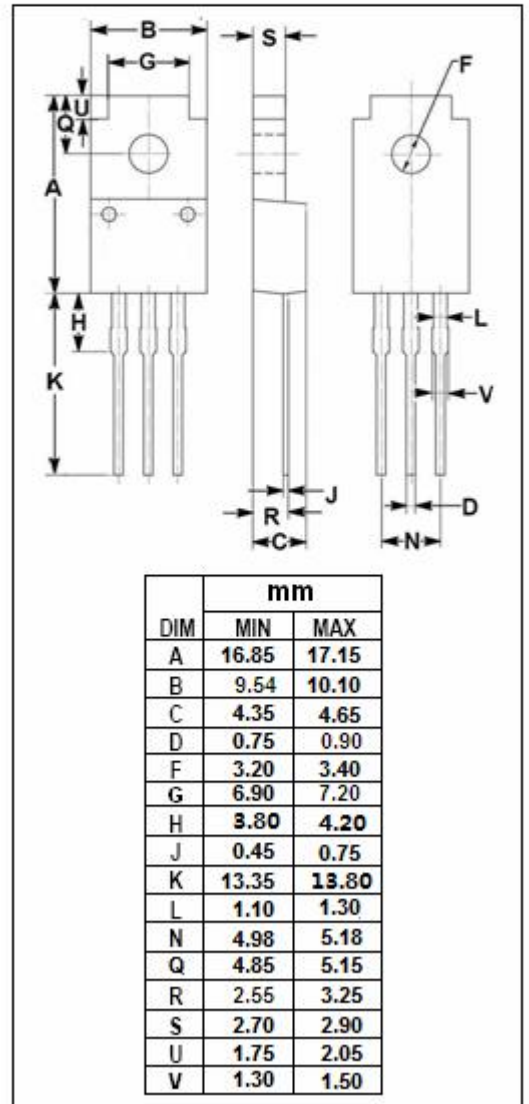
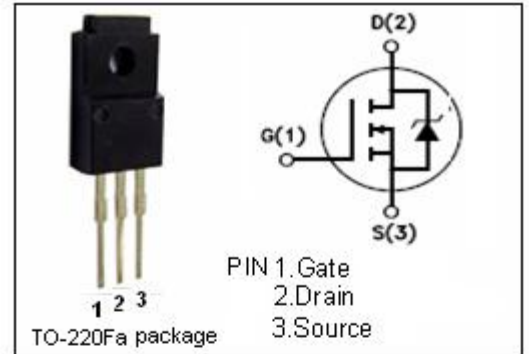
- Drain Current $-I_D=8A@ T_C=25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS}= 100V(\text{Min})$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- High speed power switching

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C=25^{\circ}C$	8	A
P_{tot}	Total Dissipation@ $T_C=25^{\circ}C$	40	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc N-Channel Mosfet Transistor**2SK844****• ELECTRICAL CHARACTERISTICS (T_c=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	100			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =0; I _D =1mA	2.0		4.0	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D = 4A			0.15	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±16V; V _{DS} = 0			±10	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V; V _{GS} = 0			0.1	mA

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